



### **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

| BV <sub>DSS</sub> | Max R <sub>DS(ON)</sub>                         | Max I <sub>D</sub><br>T <sub>A</sub> = +25°C |  |
|-------------------|---|--|--|
| -60V              | $400 \text{m}\Omega @ V_{GS} = -10V$            | -1.1A  |  |
| -00 V             | $600 \text{m}\Omega$ @ $V_{GS} = -4.5 \text{V}$ | -0.9A  |  |

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC DC converters
- Power management functions
- Relay and solenoid driving
- Motor control

### **Features**

- Fast Switching Speed
- Low Input Capacitance
- Low Gate Charge
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Available (Note 4)

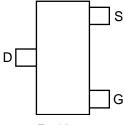
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.009 grams (Approximate)

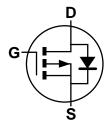




Top View



Top View Pin Out



**Equivalent Circuit** 

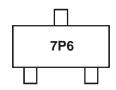
### **Ordering Information (Notes 5)**

| Processing the second s |            |                 |                   |
|--|------------|-----------------|-------------------|
| Part Number  | Compliance | Case            | Quantity per Reel |
| ZXMP6A13FQTA   | Automotive | SOT23 (Type DN) | 3,000             |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



7P6 = Product Type Marking Code



# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

| Characteristic                                  |                        |                        | Symbol                           | Value   | Unit                 |   |
|---|------------------------|------------------------|----------------------------------|---------|----------------------|---|
| Drain-Source Voltage                            |                        |                        | $V_{DSS}$                        | -60     | V                    |   |
| Gate-Source Voltage                             |                        |                        | V <sub>GS</sub>                  | ±20     | V                    |   |
| Continuous Drain Current                        | V <sub>GS</sub> = -10V | T <sub>A</sub> = +70°C | (Note 8)<br>(Note 7)<br>(Note 6) | $I_{D}$ | -1.1<br>-0.8<br>-0.9 | А |
| Pulsed Drain Current (Note 8)                   |                        |                        | I <sub>DM</sub>                  | -4.0    | A                    |   |
| Continuous Source Current (Body Diode) (Note 7) |                        |                        | Is                               | -1.2    | А                    |   |
| Pulsed Source Current (Body Diode) (Note 8)     |                        |                        | I <sub>SM</sub>                  | -4.0    | Α                    |   |

# Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

| Characteristic                                   | Symbol                            | Value       | Unit  |
|--|-----------------------------------|-------------|-------|
| Power Dissipation (Note 6)                       | D-                                | 625         | mW    |
| Linear Derating Factor                           | P <sub>D</sub>                    | 5           | mW/°C |
| Power Dissipation (Note 7)                       | Б                                 | 806         | mW    |
| Linear Derating Factor                           | P <sub>D</sub>                    | 6.5         | mW/°C |
| Thermal Resistance, Junction to Ambient (Note 6) | $R_{	heta JA}$                    | 200         | °C/W  |
| Thermal Resistance, Junction to Ambient (Note 7) | R <sub>0JA</sub>                  | 155         | °C/W  |
| Thermal Resistance, Junction to Leads (Note 9)   | R <sub>0</sub> JL                 | 194         | °C/W  |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C    |

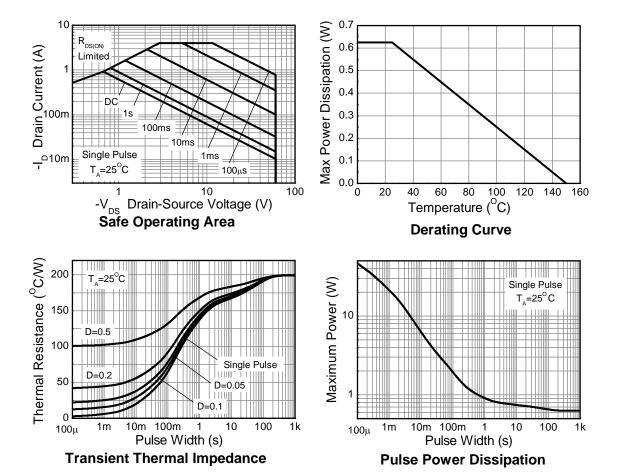
Notes:

- 6. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 7. For a device surface mounted on FR-4 PCB measured at t ≤ 5s.

  8. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05 pulse width = 10µs pulse current limited by maximum junction temperature.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).



## **Thermal Characteristics**





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

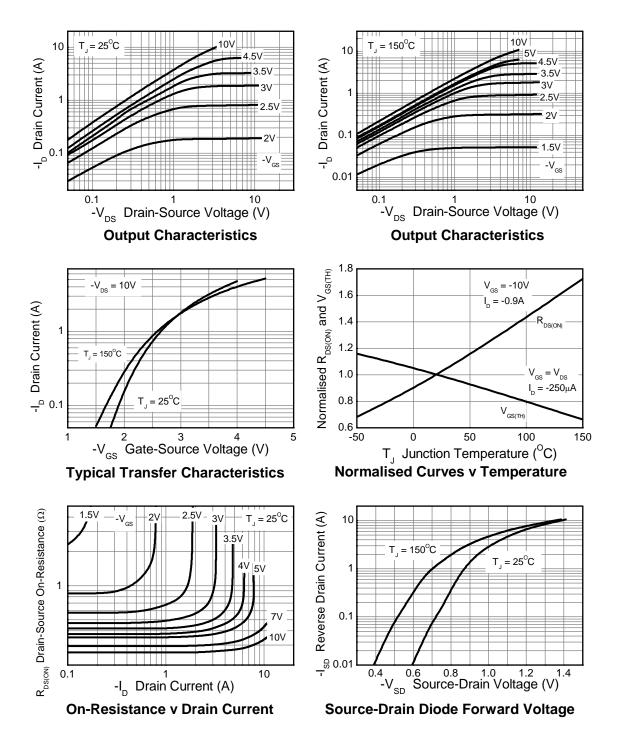
| Characteristic                              | Symbol              | Min  | Тур   | Max   | Unit | Test Condition                                       |
|---|---------------------|------|-------|-------|------|--|
| OFF CHARACTERISTICS                         |                     |      |       |       |      |  |
| Drain-Source Breakdown Voltage              | BV <sub>DSS</sub>   | -60  | _     | _     | V    | $I_D = -250\mu A, V_{GS} = 0V$                       |
| Zero Gate Voltage Drain Current             | I <sub>DSS</sub>    | _    | _     | -0.5  | μΑ   | $V_{DS} = -60V, V_{GS} = 0V$                         |
| Gate-Source Leakage                         | I <sub>GSS</sub>    | _    | _     | ±100  | nA   | $V_{GS} = \pm 20V, V_{DS} = 0V$                      |
| ON CHARACTERISTICS                          |                     |      |       |       |      | ·  |
| Gate Threshold Voltage                      | V <sub>GS(TH)</sub> | -1.0 | _     | -3.0  | V    | $I_D = -250 \mu A$ , $V_{DS} = V_{GS}$               |
| Static Drain-Source On-Resistance (Note 10) | Process             | _    |       | 0.4   | Ω    | $V_{GS} = -10V, I_D = -0.9A$                         |
| Static Brain Source on Resistance (Note 10) | R <sub>DS(ON)</sub> |      |       | 0.6   | 32   | $V_{GS} = -4.5V$ , $I_{D} = -0.8A$                   |
| Forward Transconductance (Notes 10 and 12)  | <b>g</b> fs         |      | 1.8   |       | S    | $V_{DS} = -15V, I_{D} = -0.9A$                       |
| Diode Forward Voltage (Note 10)             | $V_{SD}$            |      | -0.85 | -0.95 | V    | $T_J = +25$ °C, $I_S = -0.8$ A, $V_{GS} = 0$ V       |
| Reverse Recovery Time (Note 12)             | t <sub>RR</sub>     |      | 21.1  | _     | ns   | $T_J = +25^{\circ}C$ , $I_F = -0.9A$ ,               |
| Reverse Recovery Charge (Note 12)           | $Q_{RR}$            | _    | 19.3  | _     | nC   | di/dt = 100A/µs                                      |
| DYNAMIC CHARACTERISTICS (Note 12)           |                     |      | •     |       | •    |  |
| Input Capacitance                           | Ciss                |      | 219   | _     |      | 1/ 201/ 1/ 21/                                       |
| Output Capacitance                          | Coss                |      | 25.7  | _     | pF   | $V_{DS} = -30V, V_{GS} = 0V$<br>f = 1.0MHz           |
| Reverse Transfer Capacitance                | Crss                |      | 20.5  | _     |      |  |
| Turn-On Delay Time (Note 11)                | t <sub>D(ON)</sub>  | _    | 1.6   | _     |      |  |
| Turn-On Rise Time (Note 11)                 | t <sub>R</sub>      | _    | 2.2   | _     | ns   | $V_{DD} = -30V, I_{D} = -1A,$                        |
| Turn-Off Delay Time (Note 11)               | t <sub>D(OFF)</sub> | _    | 11.2  | _     | 115  | $R_g \cong 6.0\Omega, V_{GS} = -10V$                 |
| Turn-Off Fall Time (Note 11)                | t <sub>F</sub>      | _    | 5.7   | _     |      |  |
| Total Gate Charge (Note 11)                 | Qg                  | _    | 2.9   | _     | nC   | $V_{DS} = -30V$ , $V_{GS} = -4.5V$ , $I_{D} = -0.9A$ |
| Total Gate Charge (Note 11)                 | Qg                  | _    | 5.9   | _     |      |  |
| Gate-Source Charge (Note 11)                | Qgs                 | _    | 0.74  |       | nC   | $V_{DS} = -30V, V_{GS} = -10V,$<br>$I_{D} = -0.9A$   |
| Gate-Drain Charge (Note 11)                 | $Q_{gd}$            |      | 1.5   | _     |      | ID = -0.9A   |

Notes:

<sup>10.</sup> Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
11. Switching characteristics are independent of operating junction temperature.
12. For design aid only, not subject to production testing

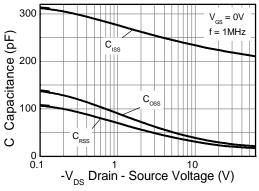


## **Typical Characteristics**

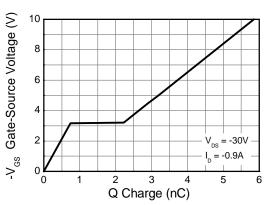




## **Typical Characteristics** (Cont.)

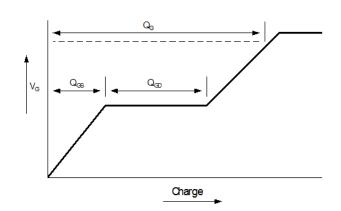


Capacitance v Drain-Source Voltage

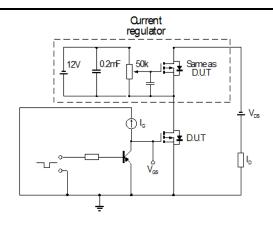


**Gate-Source Voltage v Gate Charge** 

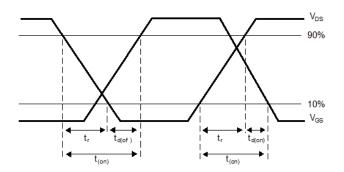
### **Test Circuits**



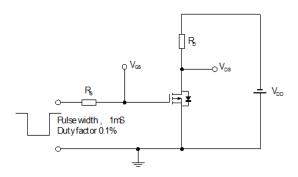
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



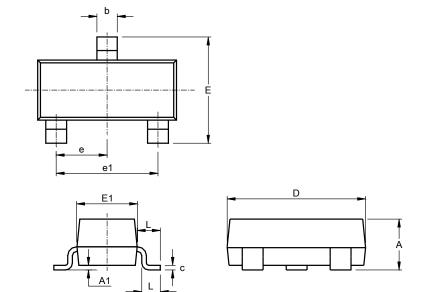
Switching time test circuit



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Type DN)

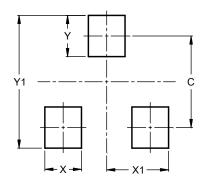


| S                    | SOT23 (Type DN) |      |      |  |  |
|----------------------|-----------------|------|------|--|--|
| Dim                  | Min             | Max  | Тур  |  |  |
| Α                    | 0.89            | 1.12 | 1.00 |  |  |
| A1                   | 0.01            | 0.10 | 0.05 |  |  |
| b                    | 0.30            | 0.51 | 0.45 |  |  |
| С                    | 0.08            | 0.20 | 0.10 |  |  |
| D                    | 2.80            | 3.04 | 3.00 |  |  |
| Е                    | 2.10            | 2.64 | 2.42 |  |  |
| E1                   | 1.20            | 1.40 | 1.37 |  |  |
| е                    | e 0.95 REF      |      |      |  |  |
| e1                   | 1.90 REF        |      |      |  |  |
| L                    | 0.25            | 0.60 | 0.30 |  |  |
| L1                   | 0.45            | 0.62 | 0.54 |  |  |
| All Dimensions in mm |                 |      |      |  |  |

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Type DN)



| Dimensions | Value (in mm) |  |  |
|------------|---------------|--|--|
| С          | 2.0           |  |  |
| Х          | 0.8           |  |  |
| X1         | 1.35          |  |  |
| Υ          | 0.9           |  |  |
| Y1         | 2.9           |  |  |



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